

Is Now Part of



# **ON Semiconductor**®

# To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="https://www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to <a href="https://www.onsemi.com">Fairchild\_questions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized applications, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an equif prese



### FDB2614

# N-Channel PowerTrench<sup>®</sup> MOSFET 200 V, 62 A, 27 m $\Omega$

#### Features

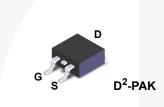
- $R_{DS(on)}$  = 22.9 m $\Omega$  (Typ.)@  $V_{GS}$  = 10 V,  $I_D$  = 31 A
- High Performance Trench technology for Extremely Low  $R_{\text{DS}(\text{on})}$
- Low Gate Charge
- High Power and Current Handing Capability

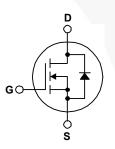
#### **General Description**

This N-Channel MOSFET is producedusing Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

#### Applications

- Synchronous Rectification
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies





#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter		FDB2614	Unit
V <sub>DS</sub>	Drain-Source Voltage		200	V
V <sub>GS</sub>	Gate-Source Voltage		± 30	V
ID	Drain Current - Continuous (T <sub>C</sub> = 2 - Continuous (T <sub>C</sub> = 7		62 39.3	A A
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	see Figure 9	A
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		145	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C	;	260 2.1	W W/°C
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
Τ <sub>L</sub>	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

#### **Thermal Characteristics**

Symbol	Parameter	FDB2614	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.48	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient (1 in <sup>2</sup> pad of 2 oz copper), Max.	40	°C/W

Ü
•
B26
6
-
4
I
Ζ
-
4
อ
E
n
e
_
Š
Š
vei
<b></b>
_
G
ñ
C
P
M
Ο
os
П
Ē
-

Π

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB2614	FDB2614	D <sup>2</sup> -PAK	330 mm	24 mm	800 units

Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Off Charac	teristics			1		
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS}$ = 0V, $I_{D}$ = 250 $\mu$ A, $T_{J}$ = 25°C	200			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C		0.2		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 200V, V_{GS} = 0V$ $V_{DS} = 200V, V_{GS} = 0V, T_J = 125^{\circ}C$			1 500	μΑ μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30V, V <sub>DS</sub> = 0V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0V			-100	nA
On Charac	teristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3.0	4.0	5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 31A		22.9	27	mΩ
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 10V, I <sub>D</sub> = 31A		72		S
Dynamic C	haracteristics					1
C <sub>iss</sub>	Input Capacitance			5435	7230	pF
C <sub>oss</sub>	Output Capacitance	│ V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V │ f = 1.0MHz		505	675	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			110	165	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time			77	165	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 100V, I_D = 62A$ $V_{GS} = 10V, R_{GEN} = 25\Omega$		284	560	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			103	220	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		162	335	ns
Qg	Total Gate Charge			76	99	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> = 100V, I <sub>D</sub> = 62A V <sub>GS</sub> = 10V		35		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)	-	18	1	nC
Drain-Sour	ce Diode Characteristics and Maximur	m Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				62	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				186	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 62A			1.2	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, I <sub>S</sub> = 62A		145		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> /dt =100A/μs		0.81		μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

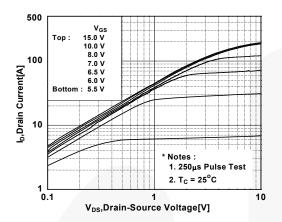
2. L = 1mH, I<sub>AS</sub> = 17A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 $\Omega$ , Starting T<sub>J</sub> = 25°C

3. I\_{SD} \leq 62A, di/dt \leq 100A/\mu s, V\_{DD} \leq BV\_{DSS}, Starting T\_J = 25°C

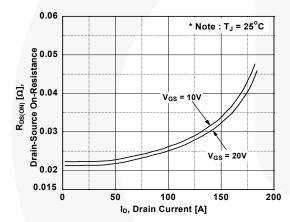
4. Essentially Independent of Operating Temperature Typical Characteristics

#### **Typical Performance Characteristics**

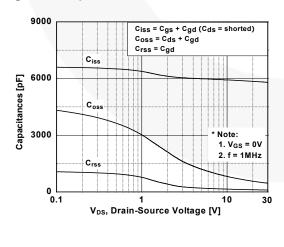
#### **Figure 1. On-Region Characteristics**



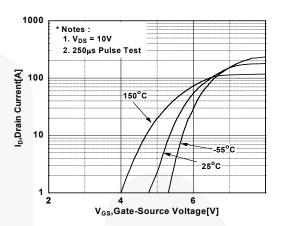








#### **Figure 2. Transfer Characteristics**





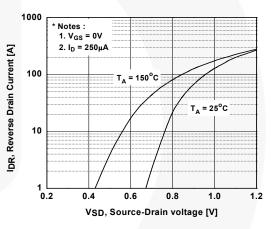
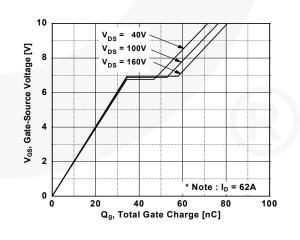
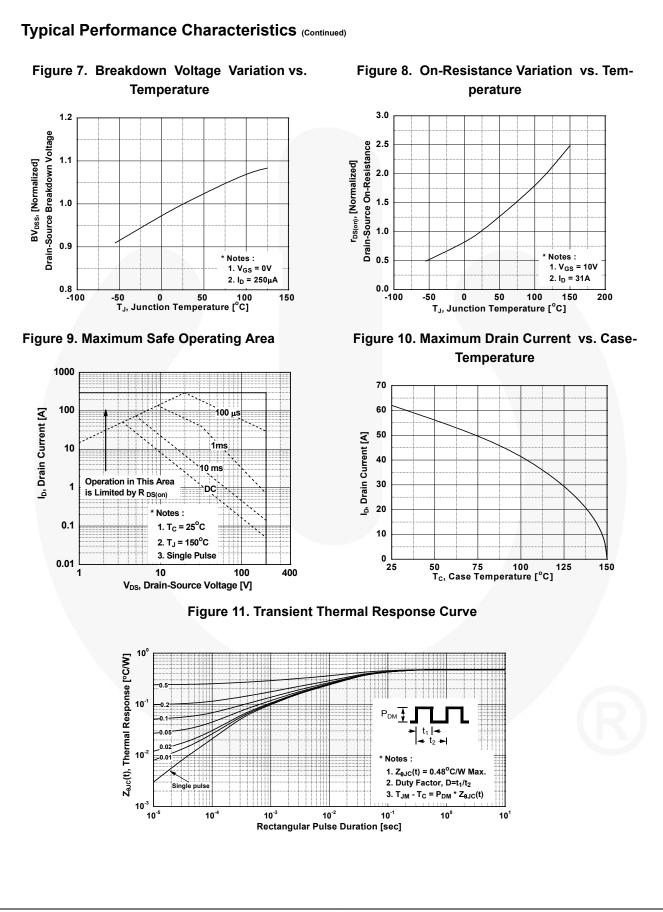
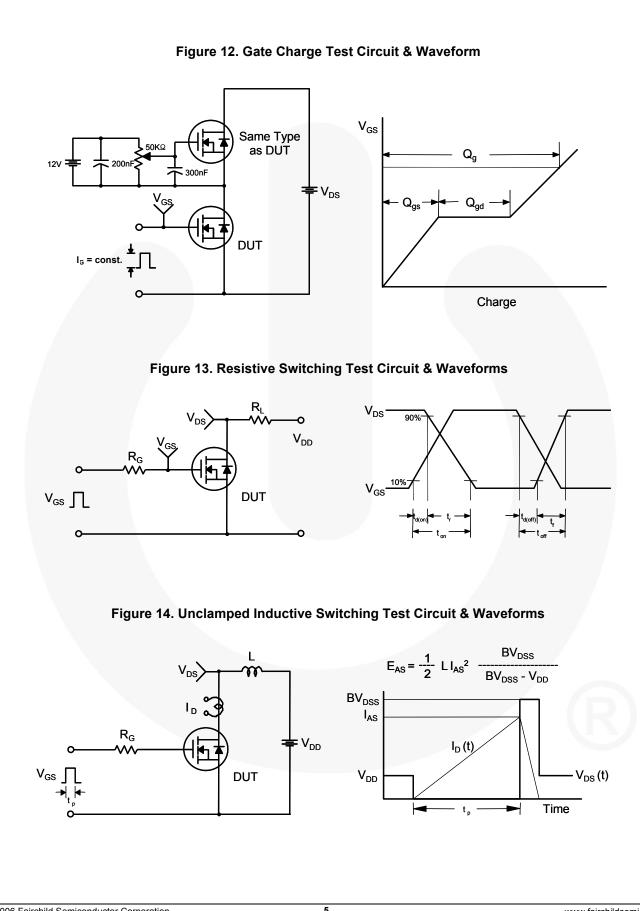


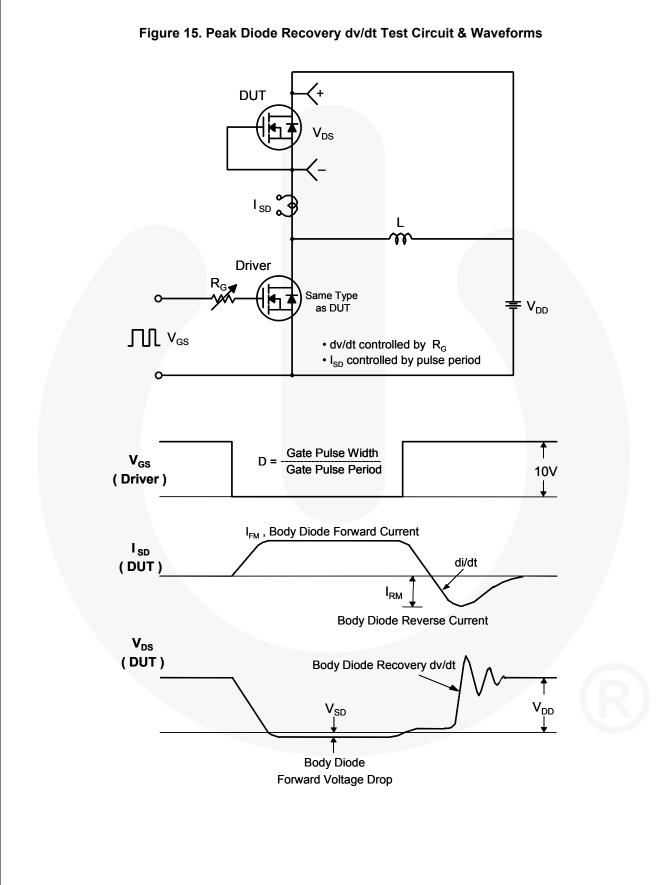
Figure 6. Gate Charge Characteristics

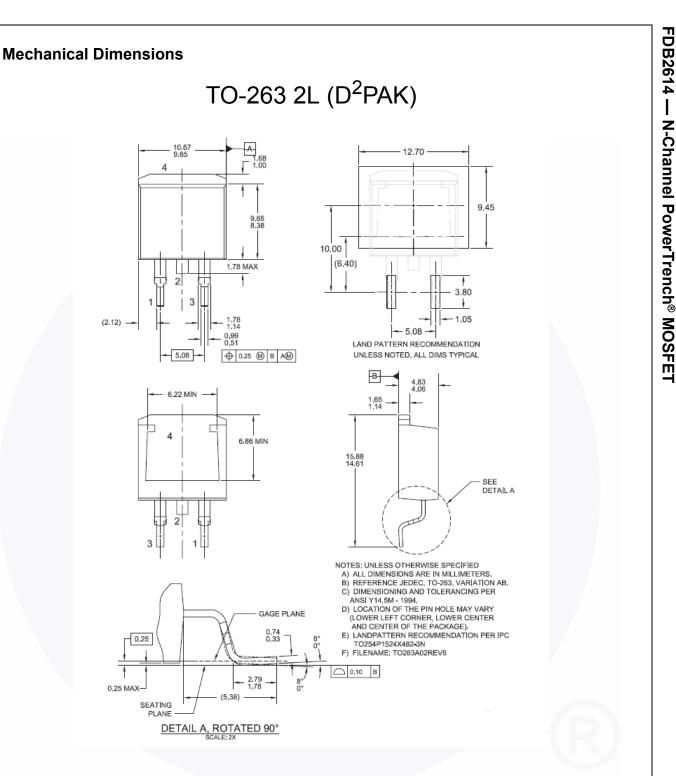




4







#### Figure 16. 2LD, TO263, Surface Mount

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TT263-002

Dimension in Millimeters

(2.12)

0.25 MAX



SEMICONDUCTOR

#### TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™	F-PFS™
AX-CAP <sup>®</sup> *	FRFET®
BitSiC™	Global Po
Build it Now™	GreenBrid
CorePLUS™	Green FP
CorePOWER™	Green FP
CROSSVOLT™	Gmax™
CTL™	GTO™
Current Transfer Logic™	IntelliMAX
DEUXPEED®	ISOPLAN
Dual Cool™	Marking S
EcoSPARK <sup>®</sup>	and Bette
EfficentMax™	MegaBuc
ESBC™	MICROCO
<b>F</b> R	MicroFET
+	MicroPak

Fairchild® Fairchild Semiconductor® FACT Quiet Series™ FACT® FAST® FastvCore™ FETBench™ FPS™

al Power Resource<sup>SM</sup> enBridge™ en FPS™ en FPS™ e-Series™ X™ ™ liMAX™ PLANAR™ king Small Speakers Sound Louder Better™ aBuck™ ROCOUPLER™ oFET™ oPak™ MicroPak2™ MillerDrive™ MotionMax™ mWSaver® OptoHiT™ **OPTOLOGIC® OPTOPLANAR<sup>®</sup>** 

 $(1)_{\mathbb{B}}$ PowerTrench® PowerXS™ Programmable Active Droop™ QFET QS™ Quiet Series™ RapidConfigure<sup>™</sup> Saving our world, 1mW/W/kW at a time™ SignalWise™ SmartMax™ SMART START™ Solutions for Your Success™ SPM<sup>®</sup> STEALTH™ SuperFET<sup>®</sup> SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS®

**E**SYSTEM<sup>®\*</sup> GENERAL TinyBoost TinyBuck® TinyCalc™ TinyLogic® TINYOPTO™ TinvPower™ TinyPWM™ TinyWire™ TranSiC™ TriFault Detect™ TRUECURRENT®\* μSerDes™ UHC® Ultra FRFET™ UniFFT™ VCX™ VisualMax™

VoltagePlus™

XS™

Sync-Lock™

FDB2614 —

**N-Channel PowerTrench® MOSFE** 

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

#### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

SvncFET™

LIFE SUPPORT POLICY FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are 1. intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

#### PRODUCT STATUS DEFINITIONS Definition of Tern

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary First Production		Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor haves against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly ori indirectly, any claim of personal injury or death

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

## **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: FDB2614



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

**Телефон:** 8 (812) 309 58 32 (многоканальный) **Факс:** 8 (812) 320-02-42 **Электронная почта:** <u>org@eplast1.ru</u> **Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.